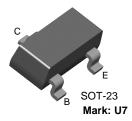


# **BSR13**

## **NPN General Purpose Amplifier**

• Sourced from process 10.



# **Absolute Maximum Ratings\*** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	0.5	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

<sup>\*</sup> This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These rating are based on a maximum junction temperature of 150 degrees C.
 These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charac	cteristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10\mu A, I_{E} = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50V, I_{E} = 0$		30	nA
		$V_{CB} = 50V, I_{E} = 0, T_{a} = 150^{\circ}C$		10	μΑ
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$		15	nA
On Charac	cteristics			•	
h <sub>FE</sub>	DC Current Gain	$I_C = 0.1 \text{mA}, V_{CE} = 10 \text{V}$ $I_C = 1.0 \text{mA}, V_{CE} = 10 \text{V}$	35 50		
		$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}$	75		
		I <sub>C</sub> = 150mA, V <sub>CF</sub> = 10V *	100	300	
		I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1.0V *	50		
		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V} *$	30		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		0.4	V
()		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		1.6	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15V		1.3	V
. ,		$I_C = 500 \text{mA}, I_B = 50 \text{V}$		2.6	
Small Sign	nal Characteristics			· · · · · ·	
f <sub>T</sub>	Curent Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz	250		
Pulse Test: Pu	lse Width ≤ 300μs, Duty Cycle ≤ 2.0%	•			

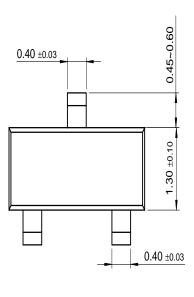
©2004 Fairchild Semiconductor Corporation

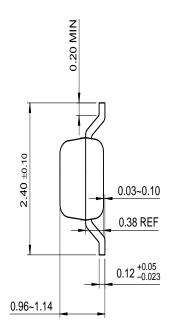
Thermal Characteristics T <sub>a</sub> =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

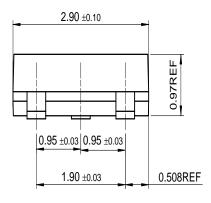
<sup>\*</sup> Device mounted on FR-4PCB 1.6" × 1.6" × 0.06".

# **Package Dimensions**

# SOT-23







Dimensions in Millimeters

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EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC <sup>®</sup>	μSerDes™	UltraFET <sup>®</sup>
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The Power Franchise®		PACMAN™	SMART START™	
Programmable Active Droop™		POP™	SPM™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

### **Definition of Terms**

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